

# Ling-Xuan Qian

## List of Publications by Year in descending order

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28  
papers

768  
citations

686830

13  
h-index

713013

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g-index

28  
all docs

28  
docs citations

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times ranked

808  
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultra-sensitive $\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ Solar-Blind Photodetector with High-Density $\text{Al@Al}_{2}\text{O}_{3}$ Core-Shell Nanoplasmonic Array. <i>Advanced Optical Materials</i> , 2022, 10, .	3.6	18
2	Localized surface plasmon-enhanced photodetection in $\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ solar-blind photodetector with Sn nanoparticles array. , 2022, , .		1
3	High Performance Flexible Visible-Blind Ultraviolet Photodetectors with Two-Dimensional Electron Gas Based on Unconventional Release Strategy. <i>ACS Nano</i> , 2021, 15, 8386-8396.	7.3	38
4	Anti-reflective porous Ge by open-circuit and lithography-free metal-assisted chemical etching. <i>Applied Surface Science</i> , 2021, 546, 149083.	3.1	9
5	Comprehensively Improved Performance of $\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ Solar-Blind Photodetector Enabled by a Homojunction with Unique Passivation Mechanisms. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 40837-40846.	4.0	45
6	Improved Detectivity of Flexible a-InGaZnO UV Photodetector via Surface Fluorine Plasma Treatment. <i>IEEE Electron Device Letters</i> , 2019, 40, 1646-1649.	2.2	28
7	Simultaneously improved sensitivity and response speed of $\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ solar-blind photodetector via localized tuning of oxygen deficiency. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	50
8	Improved Performance of Amorphous InGaMgO Metal-Semiconductor-Metal Ultraviolet Photodetector by Post Deposition Annealing in Oxygen. <i>IEEE Nanotechnology Magazine</i> , 2018, 17, 29-35.	1.1	15
9	Improved Performance of Amorphous InGaZnO Thin-Film Transistor by Hf Incorporation in $\text{La}_{2}\text{O}_{3}$ Gate Dielectric. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018, 18, 333-336.	1.5	13
10	Tailoring the Band Alignment of $\text{Ga}_{x}\text{Zn}_{1-x}\text{O}/\text{InGaZnO}$ Heterojunction for Modulation-Doped Transistor Applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800332.	0.8	4
11	Band alignment and interfacial chemical structure of the $\text{HfLaO}/\text{InGaZnO}_{4}$ heterojunction investigated by x-ray photoelectron spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 145106.	1.3	2
12	Determination of the Band Alignment of $\text{a-GZO/a-GMO}$ Heterojunction for High-Electron Mobility Transistor Application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700251.	1.2	7
13	Ultrahigh-Responsivity, Rapid-Recovery, Solar-Blind Photodetector Based on Highly Nonstoichiometric Amorphous Gallium Oxide. <i>ACS Photonics</i> , 2017, 4, 2203-2211.	3.2	254
14	$\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ solar-blind deep-ultraviolet photodetector based on annealed sapphire substrate. <i>Vacuum</i> , 2017, 140, 106-110.	1.6	63
15	$\text{MoO}_{3}$ -based bipolar switching ReRAM fabricated by atomic layer deposition. , 2017, , .		1
16	High-sensitivity $\text{In}^{2+}\text{Ga}_{2}\text{O}_{3}$ solar-blind photodetector on high-temperature pretreated c-plane sapphire substrate. <i>Optical Materials Express</i> , 2017, 7, 3643.	1.6	74
17	Amorphous InGaMgO Ultraviolet Photo-TFT with Ultrahigh Photosensitivity and Extremely Large Responsivity. <i>Materials</i> , 2017, 10, 168.	1.3	6
18	Influence of sensitization on the surface properties of PbSe thin films. , 2017, , .		0

#	ARTICLE	IF	CITATIONS
19	Effects of Ta incorporation in Y2O3 gate dielectric of InGaZnO thin-film transistor. Applied Physics Letters, 2016, 109, .	1.5	15
20	Solar-blind deep-ultraviolet photodetector based on the $\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$ thin film grown on annealed c-plane sapphire substrate. , 2016, , .		1
21	$\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$ solar-blind deep-ultraviolet photodetector based on a four-terminal structure with or without Zener diodes. AIP Advances, 2016, 6, .	0.6	32
22	$\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$ solar-blind deep-ultraviolet photodetector based on annealed sapphire substrate. , 2016, , .		1
23	The effects of $\text{O}_{2}$ annealing on the characteristics of IGMO-based UV photodetector. , 2016, , .		0
24	Improved Performance of Amorphous InGaZnO Thin-Film Transistor With $\text{Ta}_{2}\text{O}_{5}$ Gate Dielectric by Using La Incorporation. IEEE Transactions on Device and Materials Reliability, 2014, 14, 1056-1060.	1.5	26
25	Effects of Ta incorporation in La2O3 gate dielectric of InGaZnO thin-film transistor. Applied Physics Letters, 2014, 104, .	1.5	45
26	Improved Performance of InGaZnO Thin-Film Transistor With HfLaO Gate Dielectric Annealed in Oxygen. IEEE Transactions on Device and Materials Reliability, 2014, 14, 177-181.	1.5	11
27	Influence of Ar/ $\text{O}_{2}$ ratio during IGZO deposition on the electrical characteristics of a-IGZO TFT with HfLaO gate dielectric. , 2013, , .		1
28	A low-frequency noise model with carrier generation-recombination process for pentacene organic thin-film transistor. Journal of Applied Physics, 2013, 114, 044503.	1.1	8